

Amendments to the Claims:

The following listing of claims will replace any/all prior versions, and listings, of claims in the application, wherein additions are shown in underlined text and deletions are shown in strike-out format:

1. (Currently amended) A method for forming a bit line of a flash device, the method comprising the steps of:

(a) forming a barrier film, an interlayer insulation film, and a metal hard-mask film sequentially on a semiconductor substrate, on which a bit line contact plug is formed;

(b) forming a metal hard-mask film pattern for opening a bit line area corresponding to the bit line contact plug;

(c) forming a bit line trench;

(d) forming a bit line metal film on the entire structure including the metal hard-mask film to bury the bit line trench; and,

(e) removing the bit line metal film and the metal hard mask film on the interlayer insulation film with a metal material by means of CMP,

wherein the metal hard-mask film and the bit line metal film are formed using the same metal material used in step (e) so that the metal hard-mask film and the bit line metal film can be removed at the same time by the CMP.

2. (Original) The method of claim 1, further comprising between steps (c) and (d), a step of cleaning the bit line trench.

3. (Original) The method of claim 2, wherein the cleaning step comprises a dry cleaning process using plasma or a cleaning process by high-frequency sputtering.

4. (Original) The method of claim 3, wherein the dry cleaning process is performed using a mixed gas of CF₄ and O₂ and NF₃ gas, and the cleaning process by high-frequency sputtering is performed using Ar gas.

5. (Canceled).

6. (Original) The method of claim 1, the metal hard-mask film is formed using tungsten (W) with a thickness in the range of 500 Å to 1000 Å to endure significantly as an etching barrier in the subsequent process of etching the interlayer insulation film.

7. (Original) The method of claim 1, wherein step (b) comprises patterning the metal hard-mask film.

8. (Original) The method of claim 1, wherein step (c) comprises etching the interlayer insulation film and the barrier film using the metal hard-mask film pattern as an etching mask.

9. (Previously presented) The method of claim 1, wherein step (e) comprises a planarization process.